74LVT245B

3.3 V octal transceiver with direction pin (3-state) Rev. 02 — 8 May 2008 Prod

Product data sheet

General description

The 74LVT245B is a high-performance BiCMOS product designed for V_{CC} operation at 3.3 V.

This device is an octal transceiver featuring non-inverting 3-state bus compatible outputs in both send and receive directions. The control function implementation minimizes external timing requirements. The device features an output enable (OE) input for easy cascading and a direction (DIR) input for direction control.

Features 2.

- 3-state buffers
- Octal bidirectional bus interface
- Input and output interface capability to systems at 5 V supply
- TTL input and output switching levels
- Output capability: +64 mA/–32 mA
- Latch-up protection exceeds 500 mA per JEDEC Std 17
- ESD protection:
 - ◆ HBM JESD22-A114E exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V
- Bus-hold data inputs eliminate the need for external pull-up resistors for unused inputs
- Live insertion/extraction permitted
- Power-up 3-state
- No bus current loading when output is tied to 5 V bus

Ordering information

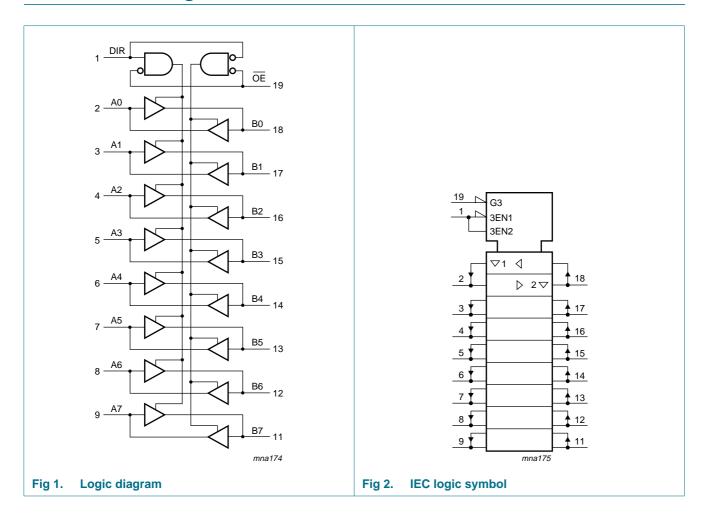
Table 1. **Ordering information**

Type number	Package							
	Temperature range	Name	Description	Version				
74LVT245BD	–40 °C to +85 °C	SO20	plastic small outline package; 20 leads; body width 7.5 mm	SOT163-1				
74LVT245BDB	–40 °C to +85 °C	SSOP20	plastic shrink small outline package; 20 leads; body width 5.3 mm	SOT339-1				
74LVT245BPW	–40 °C to +85 °C	TSSOP20	plastic thin shrink small outline package; 20 leads; body width 4.4 mm	SOT360-1				
74LVT245BBQ	–40 °C to +85 °C	DHVQFN20	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 20 terminals; body $2.5\times4.5\times0.85$ mm	SOT764-1				



3.3 V octal transceiver with direction pin (3-state)

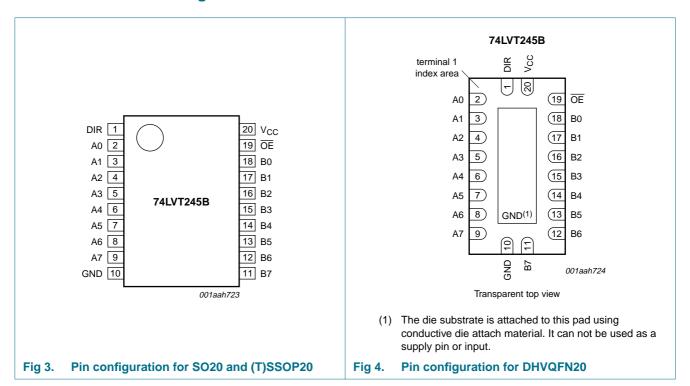
4. Functional diagram



3.3 V octal transceiver with direction pin (3-state)

5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
DIR	1	direction control
A0 to A7	2, 3, 4, 5, 6, 7, 8, 9	data input/output
GND	10	ground (0 V)
B0 to B7	18, 17, 16, 15, 14, 13, 12, 11	data input/output
ŌĒ	19	output enable input (active LOW)
V _{CC}	20	supply voltage

3.3 V octal transceiver with direction pin (3-state)

6. Functional description

Table 3. Function selection

Inputs		Inputs/outputs		
OE	DIR	An	Bn	
L	L	An = Bn	inputs	
L	Н	inputs	Bn = An	
Н	X	Z	Z	

^[1] H = HIGH voltage level;

L = LOW voltage level;

X = don't care;

Z = high impedance OFF-state.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).[1][2]

SymbolParameterConditionsMinMax V_{CC} supply voltage -0.5 $+4.6$ V_{I} input voltage $\frac{3}{2}$ -0.5 $+7.0$	
	.6 V
V ₁ input voltage [3] -0.5 +7.0	
_ 0.0	.0 V
$V_{\rm O}$ output voltage output in OFF or HIGH state $3 -0.5 +7.0$.0 V
I_{IK} input clamping current $V_I < 0$ -50 -	mA
I_{OK} output clamping current $V_O < 0$ -50 -	mA
I _O output current output in LOW state - 128	8 mA
output in HIGH state -64 -	mA
T _{stg} storage temperature –65 +15	50 °C
T _j junction temperature [2] - 150	0 °C
P_{tot} total power dissipation $T_{amb} = -40 ^{\circ}\text{C}$ to +85 $^{\circ}\text{C}$ [4] - 500	0 mW

^[1] Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

For SSOP20 and TSSOP20 packages: above 60 °C derate linearly with 5.5 mW/K.

For DHVQFN20 packages: above 60 °C derate linearly with 4.5 mW/K.

^[2] The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability. The maximum junction temperature of this integrated circuit should not exceed 150 °C.

^[3] The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.

^[4] For SO20 packages: above 70 $^{\circ}\text{C}$ derate linearly with 8 mW/K.

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8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		2.7	3.6	V
V_{I}	input voltage		0	5.5	V
I _{OH}	HIGH-level output current		-	-32	mA
I_{OL}	LOW-level output current		-	32	mA
		current duty cycle \leq 50 %; $f_i \geq$ 1 kHz	-	64	mA
T_{amb}	ambient temperature	in free air	-40	+85	°C
$\Delta t/\Delta V$	input transition rise and fall rate	output enabled	0	10	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40	°C to +85 °	C	Unit
			Min	Typ[1]	Max	
V_{IK}	input clamping voltage	$V_{CC} = 2.7 \text{ V}; I_{IK} = -18 \text{ mA}$	-1.2	-0.9	-	V
V_{IH}	HIGH-level input voltage		2.0	-	-	V
V _{IL}	LOW-level input voltage		-	-	8.0	
V_{OH}	HIGH-level output voltage	V_{CC} = 2.7 V to 3.6 V; I_{OH} = -100 μA	$V_{CC} - 0.2$	$V_{CC}-0.1$	-	V
		$V_{CC} = 2.7 \text{ V}; I_{OH} = -8 \text{ mA}$	2.4	2.5	-	
		$V_{CC} = 3.0 \text{ V}; I_{OH} = -32 \text{ mA}$	2.0	2.2	-	V
V_{OL}	LOW-level output voltage	$V_{CC} = 2.7 \text{ V}; I_{OL} = 100 \mu\text{A}$		0.1	0.2	V
		$V_{CC} = 2.7 \text{ V}; I_{OL} = 24 \text{ mA}$	-	0.3	0.5	V
		$V_{CC} = 3.0 \text{ V}; I_{OL} = 16 \text{ mA}$	-	0.25	0.4	V
		$V_{CC} = 3.0 \text{ V}; I_{OL} = 32 \text{ mA}$	-	0.3	0.5	V
		$V_{CC} = 3.0 \text{ V}; I_{OL} = 64 \text{ mA}$	-	0.4	0.55	V
I	input leakage current	control pins				
		$V_{CC} = 0 \text{ V or } 3.6 \text{ V}; V_{I} = 5.5 \text{ V}$	-	1	10	μΑ
		$V_{CC} = 3.6 \text{ V}; V_I = V_{CC} \text{ or GND}$	-	±0.1	±1	μΑ
		I/O data pins	[2]			
		$V_{CC} = 3.6 \text{ V}; V_I = 5.5 \text{ V}$	-	1	20	μΑ
		$V_{CC} = 3.6 \text{ V}; V_{I} = V_{CC}$	-	0.1	1	μΑ
		$V_{CC} = 3.6 \text{ V}; V_{I} = 0 \text{ V}$	-5	-1	-	μΑ
I _{OFF}	power-off leakage current	$V_{CC} = 0 \text{ V}$; $V_I \text{ or } V_O = 0 \text{ V to } 4.5 \text{ V}$	-	1	±100	μΑ
I _{LO}	output leakage current	$V_O = 5.5 \text{ V}$; $V_{CC} = 3.6 \text{ V}$; output HIGH	-	60	125	μΑ
I _{O(pu/pd)}	power-up/power-down output current	$V_{CC} \le 1.2 \text{ V } V_O = 0.5 \text{ V to } V_{CC};$ $V_I = \text{GND or } V_{CC}; \overline{OE} = \text{don't care}$	[3]	15	±100	μΑ
I _{BHL}	bus hold LOW current	$V_{CC} = 3.0 \text{ V}; V_I = 0.8 \text{ V}$	[<u>4]</u> 75	150	-	μΑ
I _{BHH}	bus hold HIGH current	$V_{CC} = 3.0 \text{ V}; V_I = 2.0 \text{ V}$	-150	-75	-	μΑ
I _{BHLO}	bus hold LOW overdrive current	$V_{CC} = 0 \text{ V to } 3.0 \text{ V}; V_I = 3.6 \text{ V}$	500	-	-	μΑ

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3.3 V octal transceiver with direction pin (3-state)

 Table 6.
 Static characteristics ...continued

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		-40 °C to +85 °C		С	Unit
				Min	Typ[1]	Max	
I _{BHHO}	bus hold HIGH overdrive current	$V_{CC} = 0 \text{ V to } 3.0 \text{ V}; V_I = 3.6 \text{ V}$		-	-	-500	μΑ
I_{CC}	supply current	V_{CC} = 3.6 V; V_I = V_{CC} or GND; I_O = 0 A					
		outputs HIGH		-	0.13	0.19	mA
		outputs LOW		-	3	12	mA
		outputs disabled		-	0.13	0.19	mΑ
ΔI_{CC}	additional supply current	per input pin; V_{CC} = 3.0 V to 3.6 V; one input = V_{CC} – 0.6 V others = V_{CC} or GND	<u>[5]</u>	-	0.1	0.2	mA
C _I	input capacitance	DIR and \overline{OE} inputs; $V_I = 0 \text{ V or } 3.0 \text{ V}$		-	4	-	pF
C _{I/O}	input/output capacitance	at input/output data pins, outputs disabled; $V_{I/O} = 0 \text{ V or } 3.0 \text{ V}$		-	10	-	pF

^[1] All typical values are measured at V_{CC} = 3.3 V (unless stated otherwise) and T_{amb} = 25 °C.

10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V). For test circuit see Figure 7.

Symbol	Parameter	Conditions		–40 °C to +85 °C		Unit	
			Min	Typ[1]	Max		
t _{PLH}	LOW to HIGH propagation delay	An to Bn or Bn to An	·		'		
		$V_{CC} = 2.7 \text{ V}$	-	-	4.0	ns	
		$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	1.2	2.4	3.5	ns	
t _{PHL}	HIGH to LOW propagation delay	An to Bn or Bn to An					
		$V_{CC} = 2.7 \text{ V}$	-	-	4.0	ns	
		$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	1.2	2.4	3.5	ns	
t _{PZH}	OFF-state to HIGH propagation delay	see Figure 6					
		$V_{CC} = 2.7 \text{ V}$	-	-	7.1	ns	
		$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	1.3	3.3	5.5	ns	
t_{PZL}	OFF-state to LOW propagation delay	see Figure 6					
		$V_{CC} = 2.7 \text{ V}$	-	-	6.5	ns	
		$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	1.7	3.2	5.5	ns	
t _{PHZ}	HIGH to OFF-state propagation delay	see Figure 6					
		$V_{CC} = 2.7 \text{ V}$	-	-	6.5	ns	
		V_{CC} = 3.3 V \pm 0.3 V	2.2	3.6	5.9	ns	

^[2] Unused pins at V_{CC} or GND.

^[3] This parameter is valid for any V_{CC} between 0 V and 1.2 V with a transition time of up to 10 ms. From V_{CC} = 1.2 V to V_{CC} = 3.6 V a transition time of 100 ms is permitted. This parameter is valid for T_{amb} = +25 °C only.

^[4] This is the bus hold overdrive current required to force the input to the opposite logic state.

^[5] This is the increase in supply current for each input at the specified voltage level other than V_{CC} or GND.

3.3 V octal transceiver with direction pin (3-state)

 Table 7.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V). For test circuit see Figure 7.

Symbol	Parameter	Conditions	–40 °C to +85 °C		S °C	Unit
			Min	Typ[1]	Max	
t_{PLZ}	LOW to OFF-state propagation delay	see Figure 6				
		$V_{CC} = 2.7 \text{ V}$	-	-	5.1	ns
		$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	2.2	3.4	5.0	ns

^[1] Typical values are measured at T_{amb} = 25 °C and V_{CC} = 3.3 V

11. Waveforms

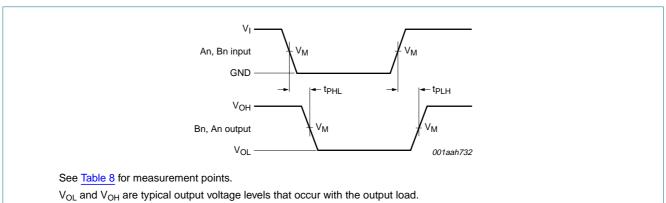
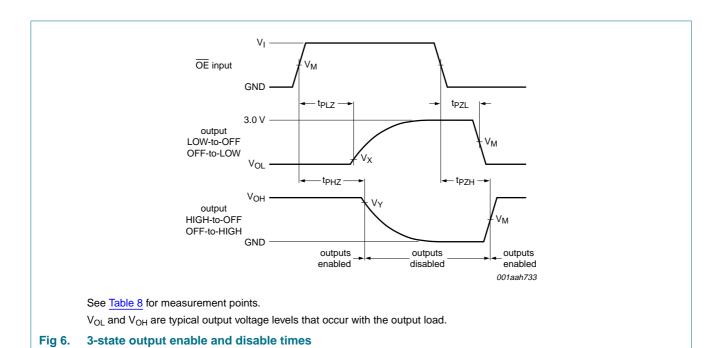


Fig 5. Input (An, Bn) to output (Bn, An) propagation delays and output transition times

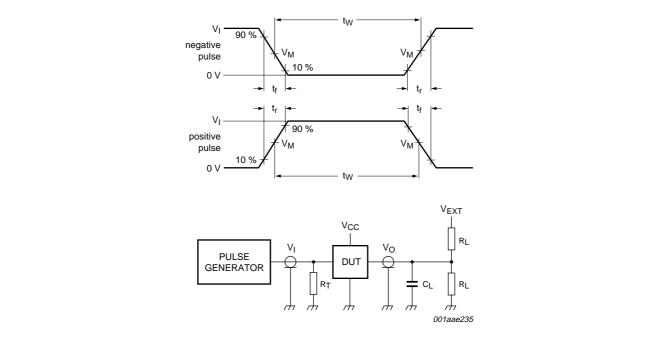


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Table 8. Measurement points

V _{CC}	Input		Output		
	V _{IN}	V _M	V _M	V _x	V _y
2.7 V to 3.6 V	GND to 2.7 V	1.5 V	1.5 V	V _{OL} + 0.3 V	V _{OH} – 0.3 V



Test data is given in Table 9.

Definitions test circuit:

R_L = Load resistance;

C_L = Load capacitance including jig and probe capacitance;

 R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator;

 V_{EXT} = External voltage for measuring switching times.

Fig 7. Test circuit for switching times

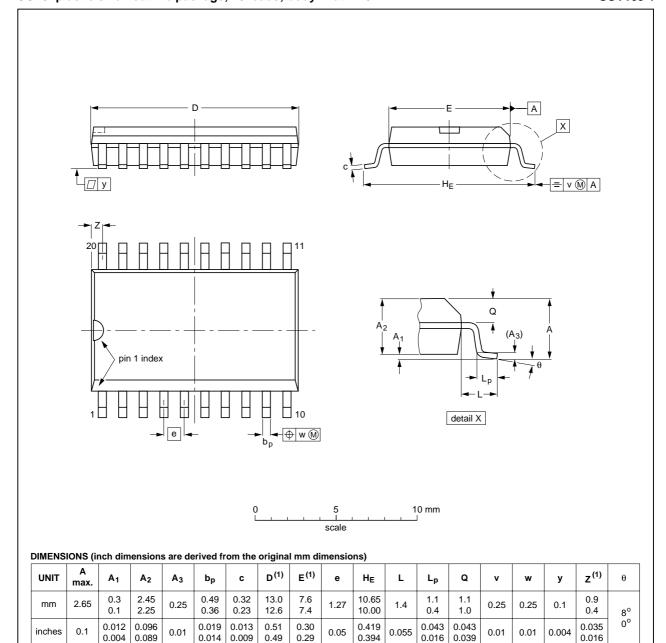
Table 9. Test data

Input		Load				V _{EXT}		
V_{I}	f _i	t _W	t _r , t _f	R_L	CL	t _{PHZ} , t _{PZH}	t_{PLZ} , t_{PZL}	t _{PLH} , t _{PHL}
2.7 V	≤ 10 MHz	500 ns	≤ 2.5 ns	500Ω	50 pF	GND	6 V	open

12. Package outline

SO20: plastic small outline package; 20 leads; body width 7.5 mm

SOT163-1



Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

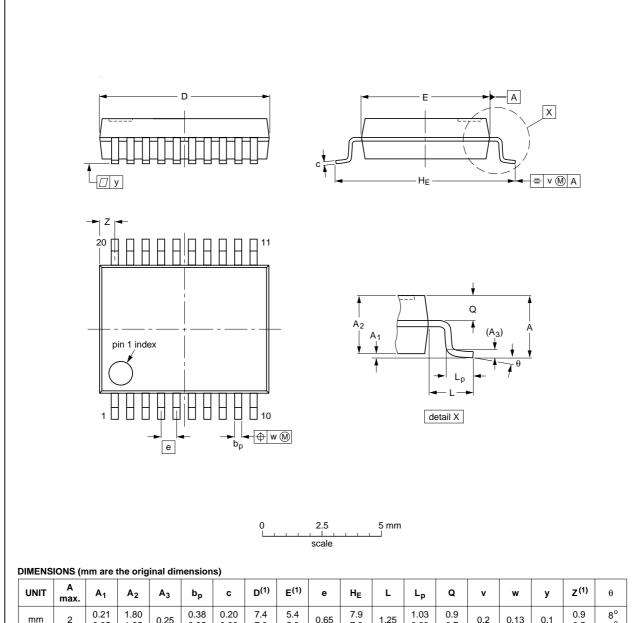
OUTLI	TLINE REFERENCES		EUROPEAN	ISSUE DATE		
VERSIO	ON	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT16	3-1	075E04	MS-013			99-12-27 03-02-19

Fig 8. Package outline SOT163-1 (SO20)

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SSOP20: plastic shrink small outline package; 20 leads; body width 5.3 mm

SOT339-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	2	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	7.4 7.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	0.9 0.5	8° 0°

Note

1. Plastic or metal protrusions of 0.2 mm maximum per side are not included.

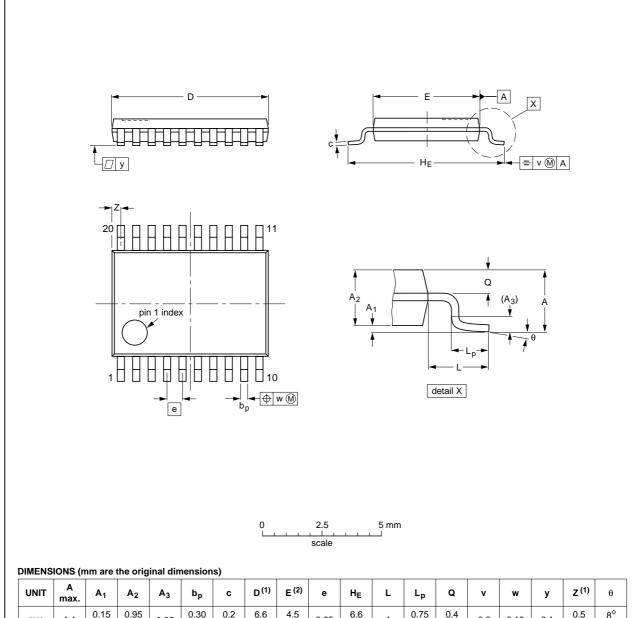
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VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT339-1		MO-150				99-12-27 03-02-19	

Package outline SOT339-1 (SSOP20) Fig 9.

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TSSOP20: plastic thin shrink small outline package; 20 leads; body width 4.4 mm

SOT360-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	U	D ⁽¹⁾	E ⁽²⁾	e	HE	٦	Lp	Q	>	w	у	Z ⁽¹⁾	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	6.6 6.4	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.5 0.2	8° 0°

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

	REFER	EUROPEAN	ISSUE DATE			
IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
	MO-153				99-12-27 03-02-19	
_	IEC				IEC JEDEC JEITA PROJECTION	

Fig 10. Package outline SOT360-1 (TSSOP20)

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DHVQFN20: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 20 terminals; body 2.5 x 4.5 x 0.85 mm SOT764-1

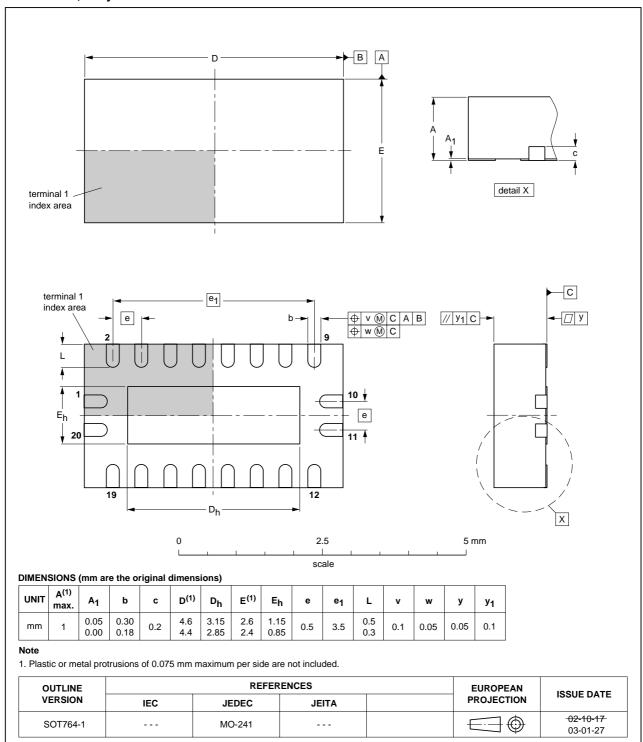


Fig 11. Package outline SOT764-1 (DHVQFN20)

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3.3 V octal transceiver with direction pin (3-state)

13. Abbreviations

Table 10. Abbreviations

Acronym	Description
BiCMOS	Bipolar Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes				
74LVT245B_2	20080508	Product data sheet	ECN07_046	74LVT245B_1				
Modifications: • The format of this data sheet has been redesigned to comply with the new identity guide NXP Semiconductors.								
	 Legal texts have been adapted to the new company name where appropriate. 							
	 DHVQFN20 	package added to Section 3 '	"Ordering information"	and Section 12 "Package outline"				
74LVT245B_1	19990319	Product specification	-	-				

3.3 V octal transceiver with direction pin (3-state)

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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74LVT245B

3.3 V octal transceiver with direction pin (3-state)

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